220 to 725 MHz Ultra-low Jitter Differential Oscillator



Features

- Any frequency between 220.000001 MHz and 725 MHz, accurate to 6 decimal places
- LVPECL, LVDS and HCSL output signaling
- 0.1ps RMS phase jitter (random) for Ethernet applications
- Contact SiTime for frequency stability as low as ±10 ppm
- Wide temperature range from -40°C to 85°C
 Contact SiTime for higher temperature range options
- Industry-standard packages: 3.2 x 2.5, 7.0 x 5.0 mm Contact SiTime for 5.0 x 3.2 mm package

Electrical Characteristics

Applications

- 100 GB Ethernet, SONET, SATA, SAS, Fibre Channel
- Telecom, networking, instrumentation, storage, servers



All Min and Max limits in the Electrical Characteristics tables are specified over temperature and rated operating voltage with standard output termination show in the termination diagrams. Typical values are at 25°C and nominal supply voltage.

Table 1. Electrical Characteristics – Common to LVPECL, LVDS and HCSL

Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition
			Freq	uency Rang	e	
Output Frequency Range	f	220.000001	-	725	MHz	Accurate to 6 decimal places
			Frequ	ency Stabili	ty	
Frequency Stability	F_stab	-10	-	+10	ppm	Inclusive of initial tolerance, operating temperature, rated power supply voltage and load variations. Contact SiTime for ± 10 ppm.
		-20	-	+20	ppm	Inclusive of initial tolerance, operating temperature, rated
		-25	-	+25	ppm	power supply voltage and load variations
		-50	-	+50	ppm	
First Year Aging	F_aging1	-	±1	-	ppm	At 25°C
			Temp	erature Ranç	ge	
Operating Temperature Range	T_use	-20	-	+70	°C	Extended Commercial
		-40	-	+85	°C	Industrial. Contact SiTime for higher temperature range options
			Sup	oply Voltage		
Supply Voltage	Vdd	2.97	3.30	3.63	V	
		2.70	3.00	3.30	V	
		2.52	2.80	3.08	V	
		2.25	2.50	2.75	V	
			Input C	Characterist	ics	
Input Voltage High	VIH	70%	-	-	Vdd	Pin 1, OE
Input Voltage Low	VIL	-	-	30%	Vdd	Pin 1, OE
Input Pull-up Impedance	Z_in	-	100	-	kΩ	Pin 1, OE logic high or logic low
			Output	Characteris	tics	
Duty Cycle	DC	45	-	55	%	
			Startup	and OE Tin	ning	
Startup Time	T_start	-	-	3.0	ms	Measured from the time Vdd reaches its rated minimum value.
OE Enable/Disable Time	T_oe	-	-	3.8	μs	f = 322.265652 MHz.

Table 2. Electrical Characteristics – LVPECL Specific

Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition	
			C	urrent Cor	nsumptio	n	
Current Consumption	ldd	-	I	94	mA	Excluding Load Termination Current, Vdd = 3.3V or 2.5V	
OE Disable Supply Current	I_OE	-	I	63	mA	OE = Low	
Output Disable Leakage Current	I_leak	-	0.15	-	μA	OE = Low	
Maximum Output Current	I_driver	-	-	32	mA	Maximum average current drawn from OUT+ or OUT-	
			Οι	utput Char	acteristic	es	
Output High Voltage	VOH	Vdd-1.1	-	Vdd-0.7	V	See Figure 2	
Output Low Voltage	VOL	Vdd-1.9	Ι	Vdd-1.5	V	See Figure 2	
Output Differential Voltage Swing	V_Swing	1.2	1.6	2.0	V	See Figure 3	
Rise/Fall Time	Tr, Tf	-	225	290	ps	20% to 80%, see Figure 2	
				Jitt	er		
RMS Phase Jitter (random)	T_phj		0.225	0.270	ps	$f=322.265625\ MHz,$ Integration bandwidth = 12 kHz to 20 MHz, all Vdds, Includes spurs. 7.0 x 5.0 mm package.	
		-	0.225	0.275	ps	$f=322.265625\ MHz,$ Integration bandwidth = 12 kHz to 20 MHz, all Vdds, Includes spurs. 3.2 x 2.5 mm package.	
		-	0.1	-	ps	f = 322.265625 MHz, IEEE802.3-2005 10GbE jitter mask integration bandwidth = 1.875 MHz to 20 MHz, Includes spurs, all Vdds	
RMS Period Jitter ^[1]	T_jitt	-	1.0	1.6	ps	f = 322.265625 MHz, VDD = 3.3V or 2.5V	

Notes:

1. Measured according to JESD65B

Table 3. Electrical Characteristics – LVDS Specific

Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition	
			C	urrent Co	nsumptio	n	
Current Consumption	ldd	-	-	89	mA	Excluding Load Termination Current, Vdd = 3.3V or 2.5V	
OE Disable Supply Current	I_OE	-	-	67	mA	OE = Low	
Output Disable Leakage Current	I_leak	-	0.15	-	μA	OE = Low	
			Οι	Itput Chai	racteristic	S	
Differential Output Voltage	VOD	250	-	455	mV	See Figure 4	
VOD Magnitude Change	ΔVOD	-	-	50	mV	See Figure 4	
Offset Voltage	VOS	1.125	-	1.375	V	See Figure 4	
VOS Magnitude Change	ΔVOS	-	-	50	mV	See Figure 4	
Rise/Fall Time	Tr, Tf	-	370	465	ps	Measured with 2 pF capacitive loading to GND, 20% to 80%, see Figure 4	
				Jitt	er		
RMS Phase Jitter (random)	T_phj	-	0.215	0.265	ps	f = 322.265625 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdds, Includes spurs. 7.0 x 5.0 mm package.	
		-	0.235	0.282	ps	f = 322.265625 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdds, Includes spurs. 3.2 x 2.5 mm package.	
		-	0.1	-	ps	f = 322.265625 MHz, IEEE802.3-2005 10GbE jitter mask integration bandwidth = 1.875 MHz to 20 MHz, Includes spurs, all Vdds	
RMS Period Jitter ^[2]	T_jitt	-	0.92	1.6	ps	f = 322.265625 MHz, VDD = 3.3V or 2.5V	

Notes: 2. Measured according to JESD65B

SiTime



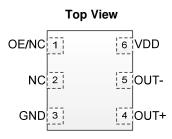
			- 0000				
Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition	
			Curr	rent Cons	umption		
Current Consumption	ldd	I	-	97	mA	Excluding Load Termination Current, Vdd = 3.3V or 2.5V	
OE Disable Supply Current	I_OE	-	-	63	mA	OE = Low	
Output Disable Leakage Current	I_leak	-	0.15	-	μA	OE = Low	
Maximum Output Current	I_driver	-	-	35	mA	Maximum average current drawn from OUT+ or OUT-	
			Outp	out Charac	teristics		
Output High Voltage	VOH	0.60	-	0.90	V	See Figure 2	
Output Low Voltage	VOL	-0.05	-	0.08	V	See Figure 2	
Output Differential Voltage Swing	V_Swing	1.2	1.4	1.9	V	See Figure 3	
Rise/Fall Time	Tr, Tf	-	360	470	ps	Measured with 2 pF capacitive loading to GND, 20% to 80%, see Figure 2	
				Jitter			
RMS Phase Jitter (random)	T_phj	-	0.215	0.270	ps	f = 322.265625 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdds, Includes spurs. 7.0 x 5.0 mm package.	
		-	0.225	0.275	ps	f = 322.265625 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdds, Includes spurs. 3.2 x 2.5 mm package.	
		-	0.1	-	ps	f = 322.265625 MHz, IEEE802.3-2005 10GbE jitter mask integration bandwidth = 1.875 MHz to 20 MHz, Includes spurs, all Vdds	
RMS Period Jitter ^[3]	T_jitt	-	1.0	1.6	ps	f = 322.265625 MHz, VDD = 3.3V or 2.5V	

Notes:

3. Measured according to JESD65

Table 5. Pin Description

Pin	Мар	Functionality						
	(OE)		H ^[4] : specified frequency output L: output is high impedance					
1	OE/NC	Non Connect (NC)	H or L or Open: No effect on output frequency or other device functions					
2	NC	NA	No Connect; Leave it floating or connect to GND for better heat dissipation					
3	GND	Power	VDD Power Supply Ground					
4	OUT+	Output	Oscillator output					
5	OUT-	Output Complementary oscillator output						
6	VDD	Power	Power supply voltage ^[5]					



SiTime

Figure 1. Pin Assignments

Notes:

4. In OE mode, a pull-up resistor of 10 k $\!\Omega$ or less is recommended if pin 1 is not externally driven.

5. A capacitor of value 0.1 μF or higher between Vdd and GND is required. An additional 10 μF capacitor between Vdd and GND is required for the best phase jitter performance



Table 6. Absolute Maximum Ratings

Attempted operation outside the absolute maximum ratings may cause permanent damage to the part. Actual performance of the IC is only guaranteed within the operational specifications, not at absolute maximum ratings.

Parameter	Min.	Max.	Unit
VDD	-0.5	4.0	V
VIH		VDD + 0.3V	V
VIL	-0.3		V
Storage Temperature	-65	150	°C
Maximum Junction Temperature		130	°C
Soldering Temperature (follow standard Pb-free soldering guidelines)		260	°C

Table 7. Thermal Considerations^[6]

Package	$ heta_{JA}$, 4 Layer Board (°C/W)	θ _{JC} , Bottom (°C/W)
3225, 6-pin	80	30
7050, 6-pin	52	19

Notes:

6. Refer to JESD51 for θ_{JA} and θ_{JC} definitions, and reference layout used to determine the θ_{JA} and θ_{JC} values in the above table.

Table 8. Maximum Operating Junction Temperature^[7]

Max Operating Temperature (ambient)	Maximum Operating Junction Temperature
70°C	95°C
85°C	110°C

Notes:

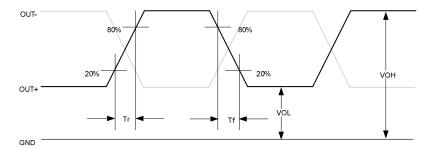
7. Datasheet specifications are not guaranteed if junction temperature exceeds the maximum operating junction temperature.

Table 9. Environmental Compliance

Parameter	Test Conditions	Value	Unit
Mechanical Shock Resistance	MIL-STD-883F, Method 2002	10,000	g
Mechanical Vibration Resistance	MIL-STD-883F, Method 2007	70	g
Soldering Temperature (follow standard Pb free soldering guidelines)	MIL-STD-883F, Method 2003	260	°C
Moisture Sensitivity Level	MSL1 @ 260°C		
Electrostatic Discharge (HBM)	HBM, JESD22-A114	2,000	V
Charge-Device Model ESD Protection	JESD220C101	750	V
Latch-up Tolerance	JESD78 Con	npliant	



Waveform Diagrams





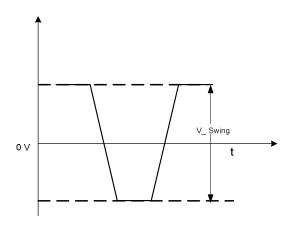


Figure 3. LVPECL/HCSL Voltage Levels across Differential Pair

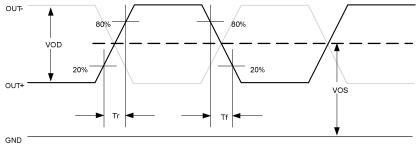


Figure 4. LVDS Voltage Levels per Differential Pin (OUT+/OUT-)



Termination Diagrams

LVPECL:

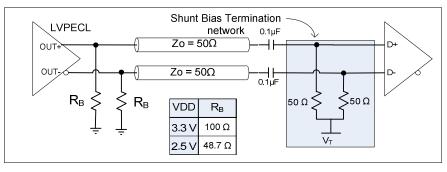


Figure 5. LVPECL with AC-coupled termination

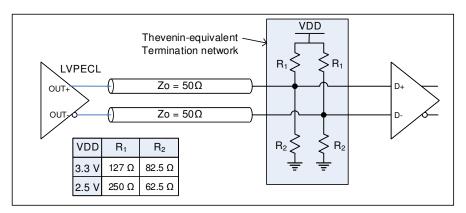


Figure 6. LVPECL DC-coupled load termination with Thevenin equivalent network

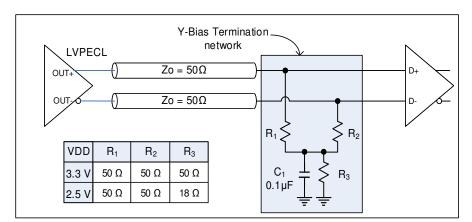


Figure 7. LVPECL with Y-Bias termination



Termination Diagrams (Continued)

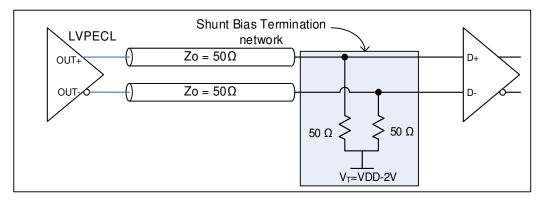


Figure 8. LVPECL with DC-coupled parallel shunt load termination



Termination Diagrams (Continued)

LVDS:

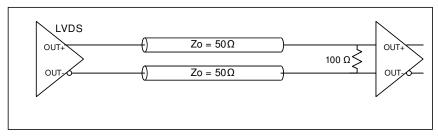


Figure 9. LVDS single DC termination at the load

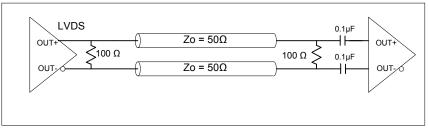


Figure 10. LVDS double AC termination with capacitor close to the load

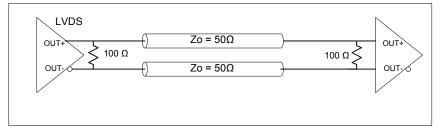


Figure 11. LVDS double DC termination



Termination Diagrams (Continued)

HCSL:

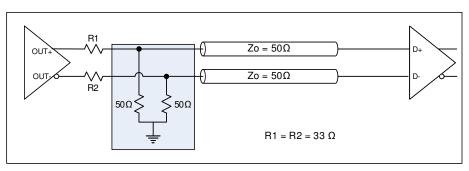
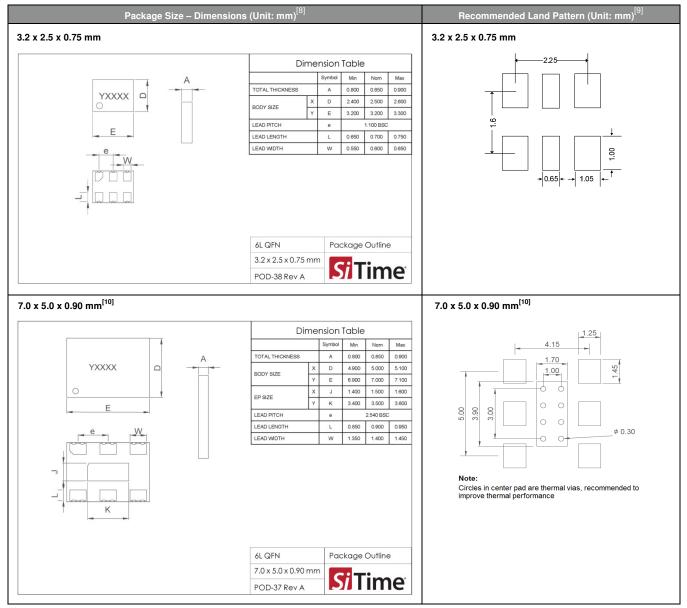


Figure 12. HCSL interface termination



Dimensions and Patterns



Notes:

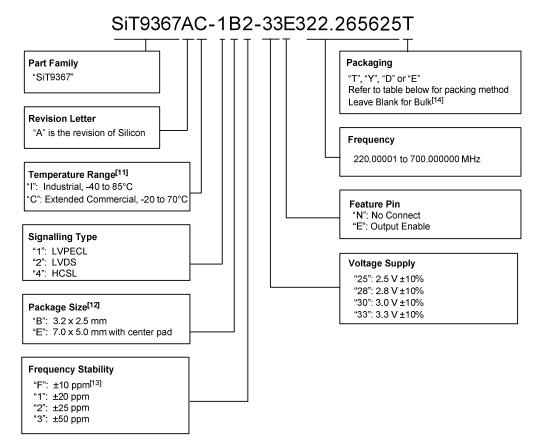
8. Top Marking: Y denotes manufacturing origin and XXXX denotes manufacturing lot number. The value of "Y" will depend on the assembly location of the device.

9. A capacitor of value 0.1 µF or higher between Vdd and GND is required. An additional 10 µF capacitor between Vdd and GND is required for the best phase jitter performance

10. The center pad has no electrical function. Soldering down the center pad to the GND is recommended for best thermal dissipation, but is optional.



Ordering Information



Notes:

- 11. Contact SiTime for higher temperature range options
- 12. Contact SiTime for 5.0 x 3.2 mm package
- 13. Contact SiTime for \pm 10 ppm option
- 14. Bulk is available for sampling only

Table 10. Ordering Codes for Supported Tape & Reel Packing Method

Device Size (mm x mm)	8 mm T&R (3ku)	8 mm T&R (1ku)	12 mm T&R (3ku)	12 mm T&R (1ku)	16 mm T&R (3ku)	16 mm T&R (1ku)
7.0 x 5.0	—	_	—	—	Т	Y
3.2 x 2.5	D	E	Т	Y	_	—



Table 11 .Revision History

Revision	Release Date	Change Summary
1.0	09/06/2017	Final release

SiTime Corporation, 5451 Patrick Henry Drive, Santa Clara, CA 95054, USA | Phone: +1-408-328-4400 | Fax: +1-408-328-4439

© SiTime Corporation 2017. The information contained herein is subject to change at any time without notice. SiTime assumes no responsibility or liability for any loss, damage or defect of a Product which is caused in whole or in part by (i) use of any circuitry other than circuitry embodied in a SiTime product, (ii) misuse or abuse including static discharge, neglect or accident, (iii) unauthorized modification or repairs which have been soldered or altered during assembly and are not capable of being tested by SiTime under its normal test conditions, or (iv) improper installation, storage, handling, warehousing or transportation, or (v) being subjected to unusual physical, thermal, or electrical stress.

Disclaimer: SiTime makes no warranty of any kind, express or implied, with regard to this material, and specifically disclaims any and all express or implied warranties, either in fact or by operation of law, statutory or otherwise, including the implied warranties of merchantability and fitness for use or a particular purpose, and any implied warranty arising from course of dealing or usage of trade, as well as any common-law duties relating to accuracy or lack of negligence, with respect to this material, any SiTime product and any product documentation. Products sold by SiTime are not suitable or intended to be used in a life support application or component, to operate nuclear facilities, or in other mission critical applications where human life may be involved or at stake. All sales are made conditioned upon compliance with the critical uses policy set forth below.

CRITICAL USE EXCLUSION POLICY

BUYER AGREES NOT TO USE SITIME'S PRODUCTS FOR ANY APPLICATION OR IN ANY COMPONENTS USED IN LIFE SUPPORT DEVICES OR TO OPERATE NUCLEAR FACILITIES OR FOR USE IN OTHER MISSION-CRITICAL APPLICATIONS OR COMPONENTS WHERE HUMAN LIFE OR PROPERTY MAY BE AT STAKE.

SiTime owns all rights, title and interest to the intellectual property related to SiTime's products, including any software, firmware, copyright, patent, or trademark. The sale of SiTime products does not convey or imply any license under patent or other rights. SiTime retains the copyright and trademark rights in all documents, catalogs and plans supplied pursuant to or ancillary to the sale of products or services by SiTime. Unless otherwise agreed to in writing by SiTime, any reproduction, modification, translation, compilation, or representation of this material shall be strictly prohibited.